

# IRF8714GPbF

## Applications

- Control MOSFET of Sync-Buck Converters used for Notebook Processor Power
- Control MOSFET for Isolated DC-DC Converters in Networking Systems

## Benefits

- Very Low Gate Charge
- Very Low  $R_{DS(on)}$  at 4.5V  $V_{GS}$
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- 20V  $V_{GS}$  Max. Gate Rating
- 100% tested for Rg
- Lead-Free
- Halogen-Free

## Description

The IRF8714GPbF incorporates the latest HEXFET Power MOSFET Silicon Technology into the industry standard SO-8 package. The IRF8714GPbF has been optimized for parameters that are critical in synchronous buck operation including  $R_{ds(on)}$  and gate charge to reduce both conduction and switching losses. The reduced total losses make this product ideal for high efficiency DC-DC converters that power the latest generation of processors for Notebook and Netcom applications.

## Absolute Maximum Ratings

|                                | Parameter                                       | Max.         | Units               |
|--------------------------------|-------------------------------------------------|--------------|---------------------|
| $V_{DS}$                       | Drain-to-Source Voltage                         | 30           | V                   |
| $V_{GS}$                       | Gate-to-Source Voltage                          | $\pm 20$     |                     |
| $I_D @ T_A = 25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ | 14           | A                   |
| $I_D @ T_A = 70^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ | 11           |                     |
| $I_{DM}$                       | Pulsed Drain Current ①                          | 110          |                     |
| $P_D @ T_A = 25^\circ\text{C}$ | Power Dissipation                               | 2.5          | W                   |
| $P_D @ T_A = 70^\circ\text{C}$ | Power Dissipation                               | 1.6          |                     |
|                                | Linear Derating Factor                          | 0.02         | W/ $^\circ\text{C}$ |
| $T_J$                          | Operating Junction and                          | -55 to + 150 | $^\circ\text{C}$    |
| $T_{STG}$                      | Storage Temperature Range                       |              |                     |

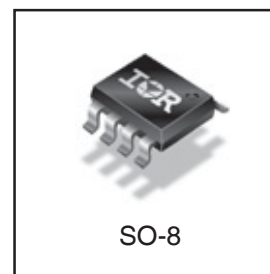
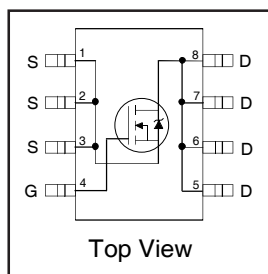
## Thermal Resistance

|                 | Parameter                | Typ. | Max. | Units              |
|-----------------|--------------------------|------|------|--------------------|
| $R_{\theta JL}$ | Junction-to-Drain Lead ⑤ | —    | 20   | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Junction-to-Ambient ④    | —    | 50   |                    |

Notes ① through ⑤ are on page 9  
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## HEXFET® Power MOSFET

| $V_{DS}$ | $R_{DS(on)}$ max                          | Qg    |
|----------|-------------------------------------------|-------|
| 30V      | $8.7\text{m}\Omega @ V_{GS} = 10\text{V}$ | 8.1nC |



# IRF8714GPbF

International  
IR Rectifier

Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

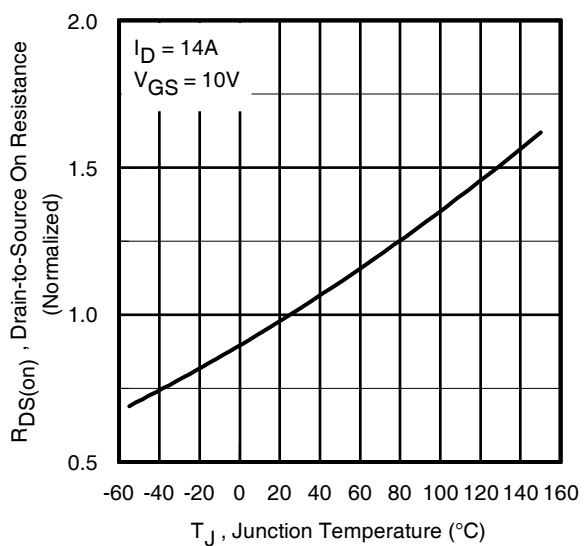
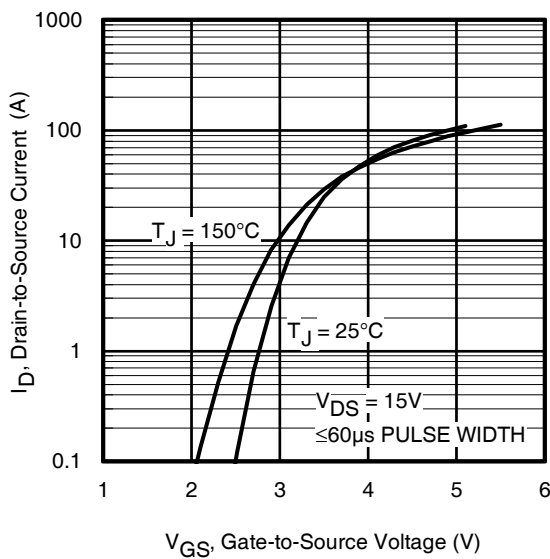
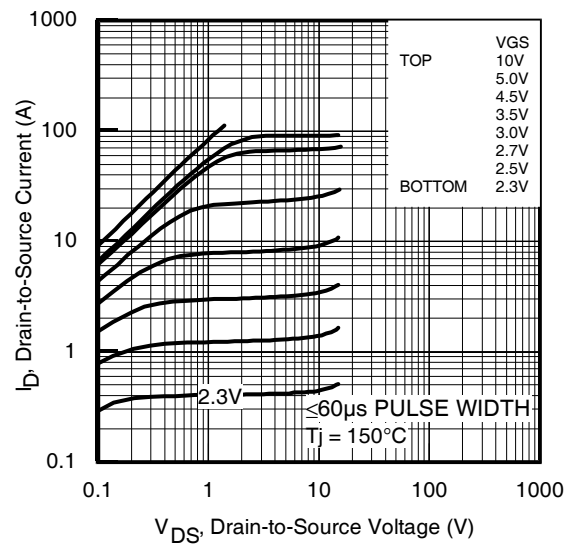
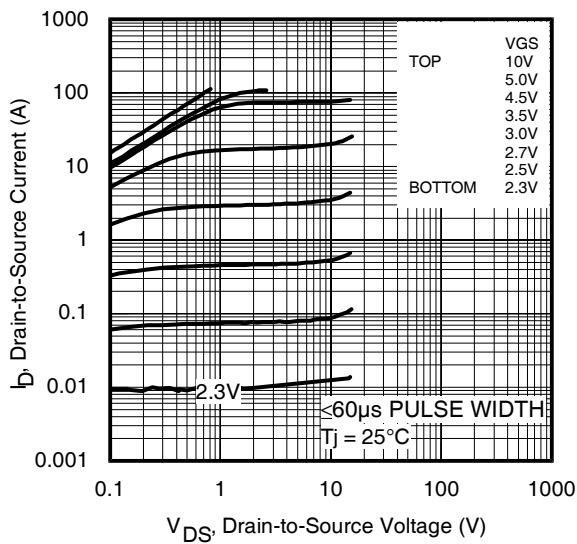
|                              | Parameter                                  | Min. | Typ.  | Max. | Units                | Conditions                                                                       |
|------------------------------|--------------------------------------------|------|-------|------|----------------------|----------------------------------------------------------------------------------|
| $BV_{DSS}$                   | Drain-to-Source Breakdown Voltage          | 30   | —     | —    | V                    | $V_{GS} = 0V, I_D = 250\mu A$                                                    |
| $\Delta BV_{DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient        | —    | 0.021 | —    | V/ $^\circ\text{C}$  | Reference to $25^\circ\text{C}, I_D = 1mA$                                       |
| $R_{DS(on)}$                 | Static Drain-to-Source On-Resistance       | —    | 7.1   | 8.7  | $m\Omega$            | $V_{GS} = 10V, I_D = 14A$ ③                                                      |
|                              |                                            | —    | 10.9  | 13   |                      | $V_{GS} = 4.5V, I_D = 11A$ ③                                                     |
| $V_{GS(th)}$                 | Gate Threshold Voltage                     | 1.35 | 1.80  | 2.35 | V                    | $V_{DS} = V_{GS}, I_D = 25\mu A$                                                 |
| $\Delta V_{GS(th)}$          | Gate Threshold Voltage Coefficient         | —    | -6.0  | —    | mV/ $^\circ\text{C}$ | $V_{DS} = V_{GS}, I_D = 25\mu A$                                                 |
| $I_{DSS}$                    | Drain-to-Source Leakage Current            | —    | —     | 1.0  | $\mu A$              | $V_{DS} = 24V, V_{GS} = 0V$                                                      |
|                              |                                            | —    | —     | 150  |                      | $V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$                             |
| $I_{GSS}$                    | Gate-to-Source Forward Leakage             | —    | —     | 100  | nA                   | $V_{GS} = 20V$                                                                   |
|                              | Gate-to-Source Reverse Leakage             | —    | —     | -100 |                      | $V_{GS} = -20V$                                                                  |
| $g_{fs}$                     | Forward Transconductance                   | 71   | —     | —    | S                    | $V_{DS} = 15V, I_D = 11A$                                                        |
| $Q_g$                        | Total Gate Charge                          | —    | 8.1   | 12   | nC                   | $V_{DS} = 15V$<br>$V_{GS} = 4.5V$<br>$I_D = 11A$<br>See Figs. 15 & 16            |
| $Q_{gs1}$                    | Pre-V <sub>th</sub> Gate-to-Source Charge  | —    | 1.9   | —    |                      |                                                                                  |
| $Q_{gs2}$                    | Post-V <sub>th</sub> Gate-to-Source Charge | —    | 1.0   | —    |                      |                                                                                  |
| $Q_{gd}$                     | Gate-to-Drain Charge                       | —    | 3.0   | —    |                      |                                                                                  |
| $Q_{godr}$                   | Gate Charge Overdrive                      | —    | 2.2   | —    |                      |                                                                                  |
| $Q_{sw}$                     | Switch Charge ( $Q_{gs2} + Q_{gd}$ )       | —    | 4.0   | —    | nC                   | $V_{DS} = 16V, V_{GS} = 0V$                                                      |
| $Q_{oss}$                    | Output Charge                              | —    | 4.8   | —    |                      |                                                                                  |
| $R_g$                        | Gate Resistance                            | —    | 1.6   | 2.6  | $\Omega$             |                                                                                  |
| $t_{d(on)}$                  | Turn-On Delay Time                         | —    | 10    | —    | ns                   | $V_{DD} = 15V, V_{GS} = 4.5V$<br>$I_D = 11A$<br>$R_G = 1.8\Omega$<br>See Fig. 18 |
| $t_r$                        | Rise Time                                  | —    | 9.9   | —    |                      |                                                                                  |
| $t_{d(off)}$                 | Turn-Off Delay Time                        | —    | 11    | —    |                      |                                                                                  |
| $t_f$                        | Fall Time                                  | —    | 5.0   | —    |                      |                                                                                  |
| $C_{iss}$                    | Input Capacitance                          | —    | 1020  | —    | pF                   | $V_{GS} = 0V$                                                                    |
| $C_{oss}$                    | Output Capacitance                         | —    | 220   | —    |                      | $V_{DS} = 15V$                                                                   |
| $C_{rss}$                    | Reverse Transfer Capacitance               | —    | 110   | —    |                      | $f = 1.0MHz$                                                                     |

## Avalanche Characteristics

|          | Parameter                       | Typ. | Max. | Units |
|----------|---------------------------------|------|------|-------|
| $E_{AS}$ | Single Pulse Avalanche Energy ② | —    | 65   | mJ    |
| $I_{AR}$ | Avalanche Current ①             | —    | 11   | A     |

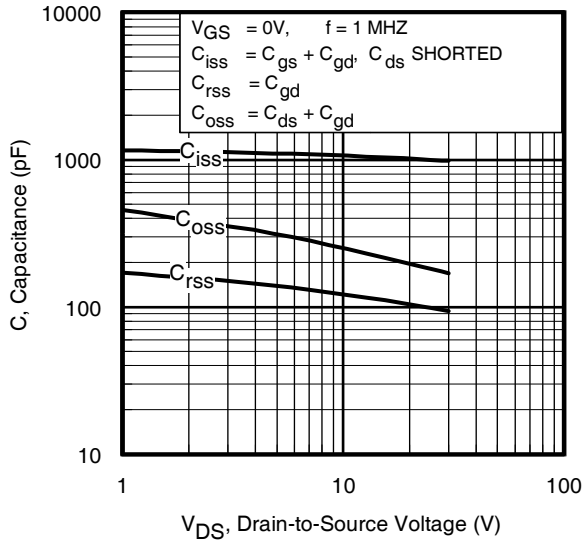
## Diode Characteristics

|          | Parameter                                 | Min.                                                                 | Typ. | Max. | Units | Conditions                                                              |
|----------|-------------------------------------------|----------------------------------------------------------------------|------|------|-------|-------------------------------------------------------------------------|
| $I_S$    | Continuous Source Current<br>(Body Diode) | —                                                                    | —    | 3.1  | A     | MOSFET symbol<br>showing the<br>integral reverse<br>p-n junction diode. |
| $I_{SM}$ | Pulsed Source Current<br>(Body Diode) ①   | —                                                                    | —    | 110  |       |                                                                         |
| $V_{SD}$ | Diode Forward Voltage                     | —                                                                    | —    | 1.0  | V     | $T_J = 25^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ③                      |
| $t_{rr}$ | Reverse Recovery Time                     | —                                                                    | 14   | 21   | ns    | $T_J = 25^\circ\text{C}, I_F = 11A, V_{DD} = 15V$                       |
| $Q_{rr}$ | Reverse Recovery Charge                   | —                                                                    | 15   | 23   | nC    | $di/dt = 300A/\mu s$ ③                                                  |
| $t_{on}$ | Forward Turn-On Time                      | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) |      |      |       |                                                                         |

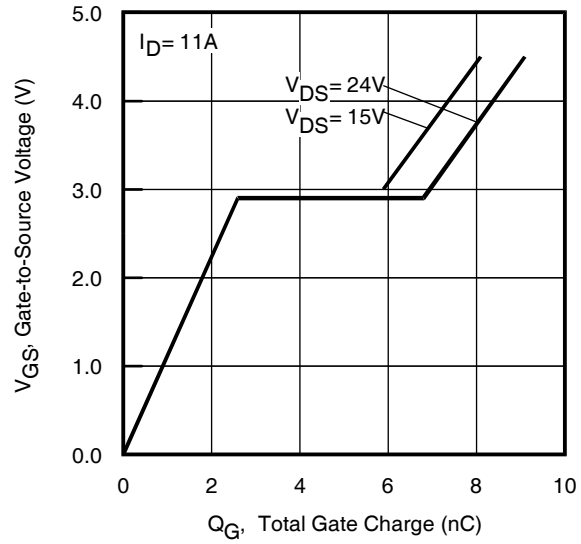


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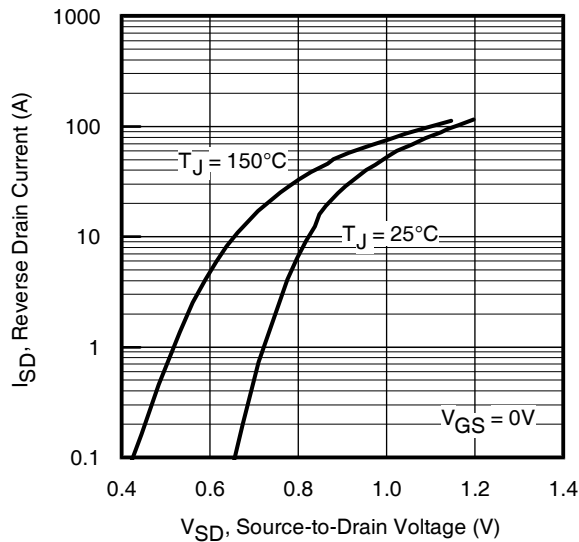
International  
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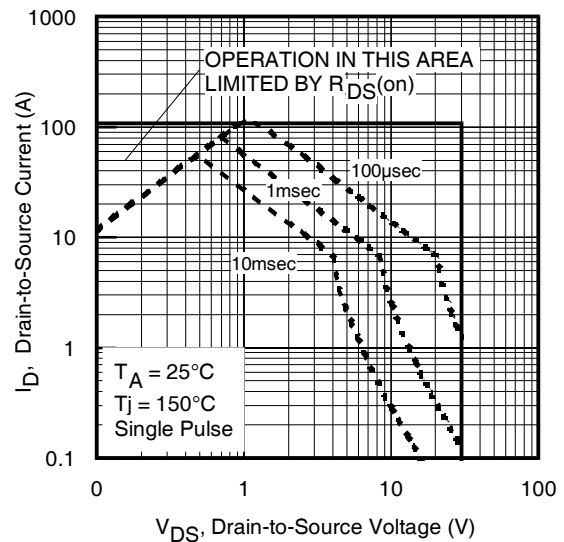
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



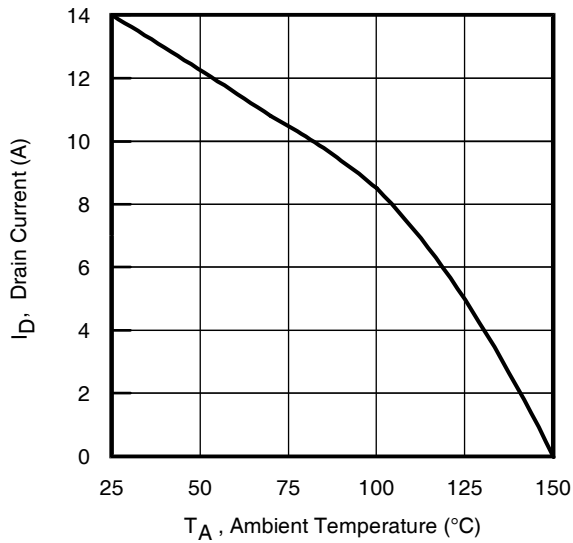
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



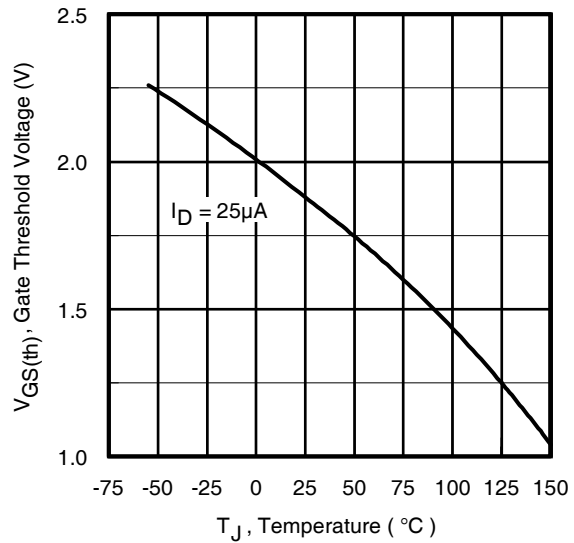
**Fig 7.** Typical Source-Drain Diode Forward Voltage



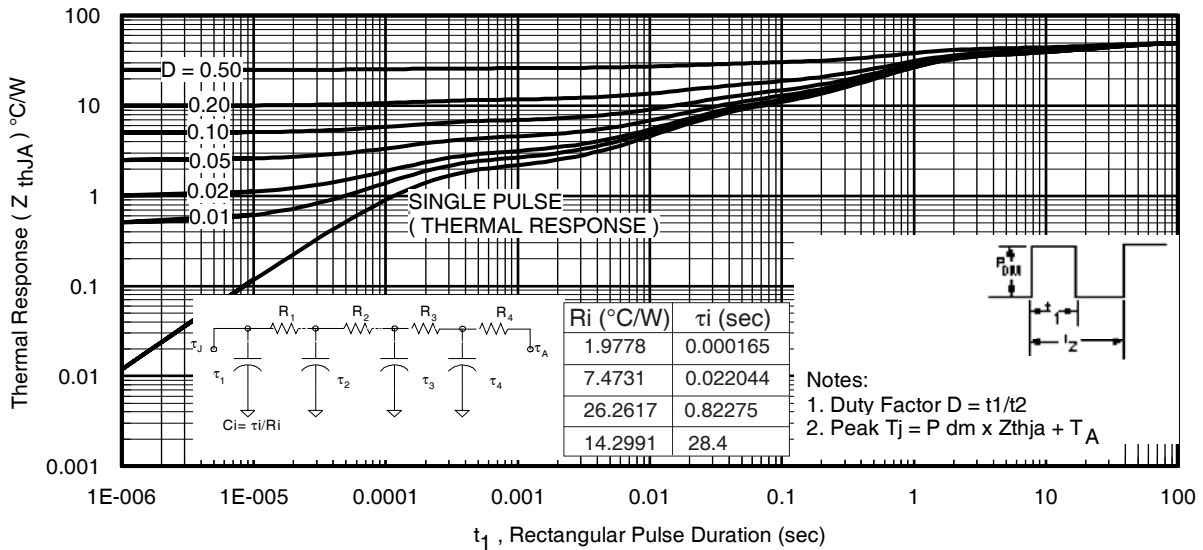
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current vs. Ambient Temperature



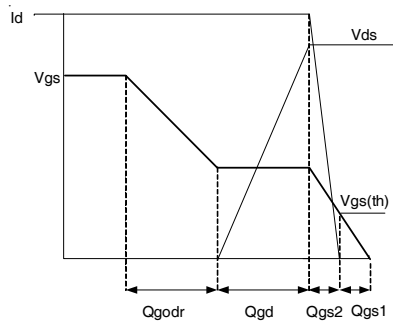
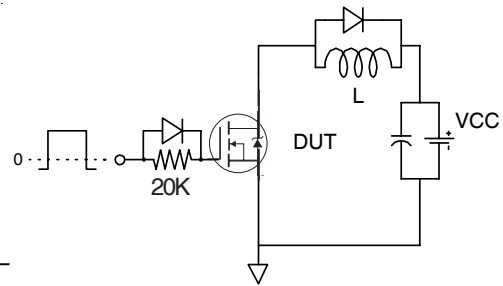
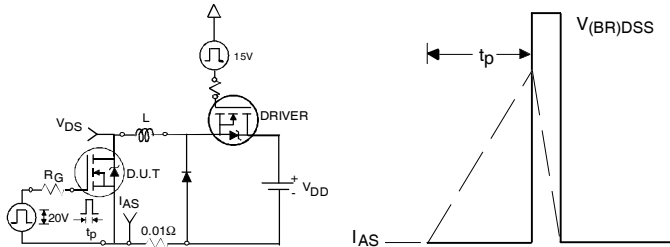
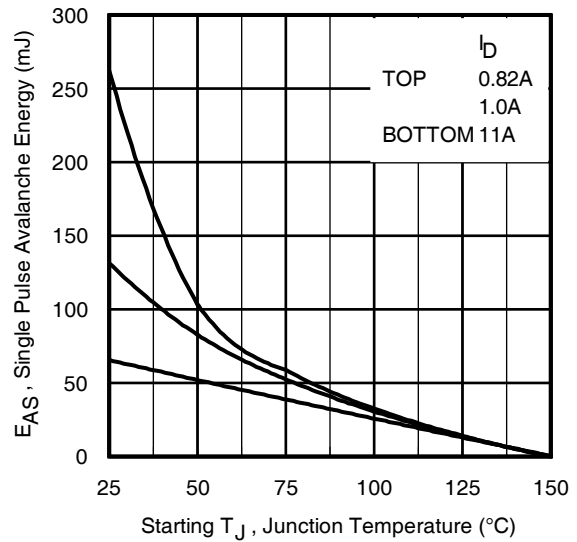
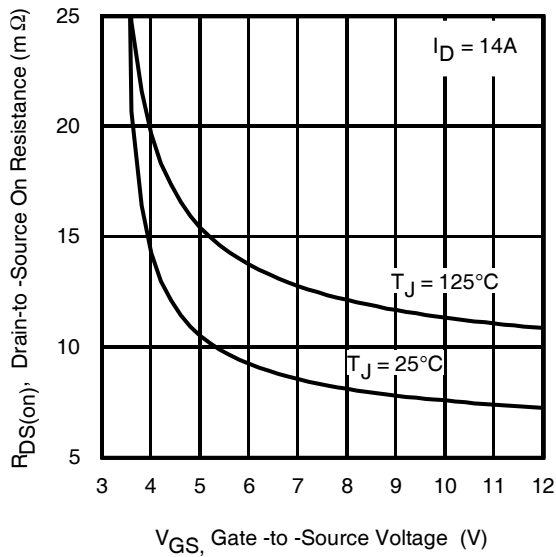
**Fig 10.** Threshold Voltage vs. Temperature

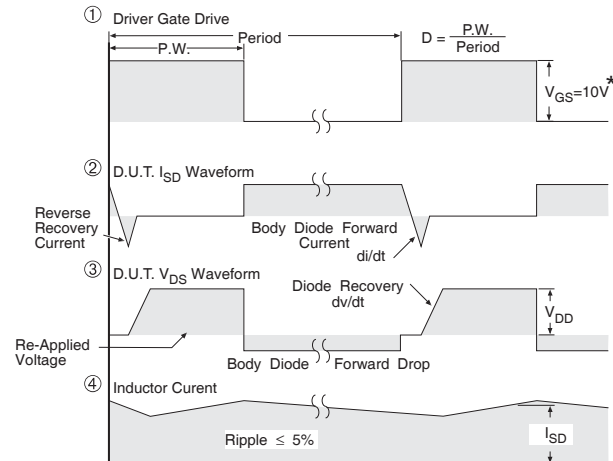
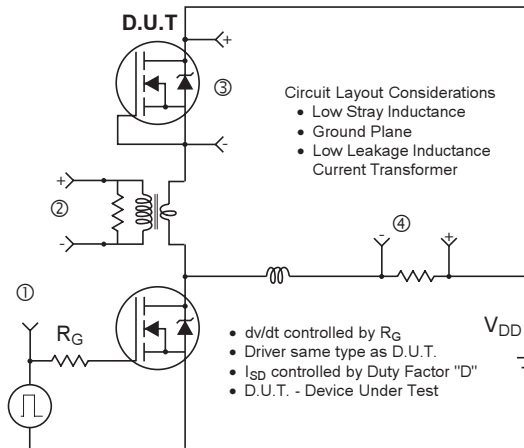


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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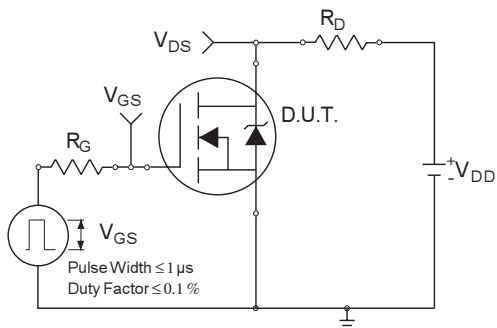
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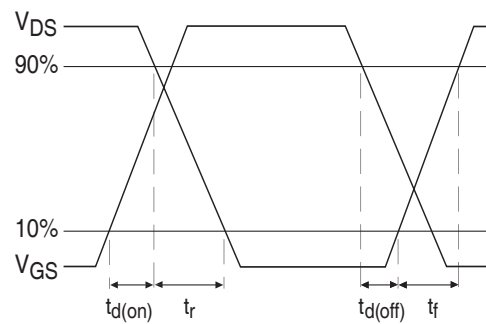


\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 17. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



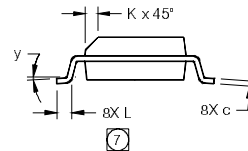
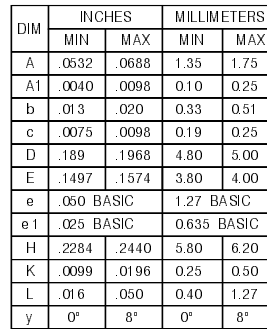
**Fig 18a. Switching Time Test Circuit**



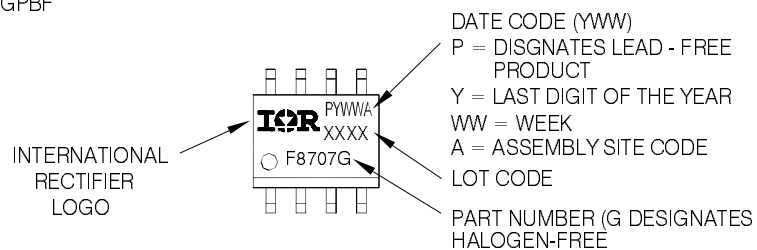
**Fig 18b. Switching Time Waveforms**

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Dimensions are shown in millimeters (inches)



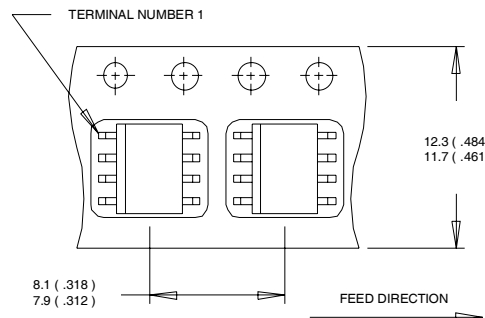
EXAMPLE: THIS IS AN IRF8707GPBF



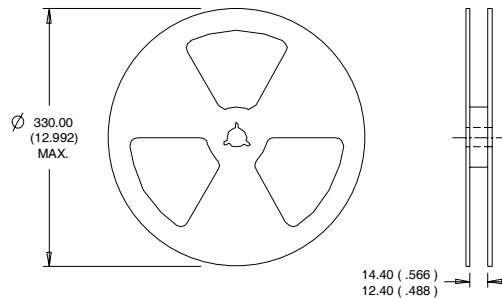
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## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1.1\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 11\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board.
- ⑤  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .

**Note:** For the most current drawing please refer to IR website at <http://www.irf.com/package>

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualification Standards can be found on IR's Web site.

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